

Features

- Uses PingWei advanced PerfectMOS2 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to AEC-Q101 criteria



100% DVDS Tested
100% Avalanche Tested

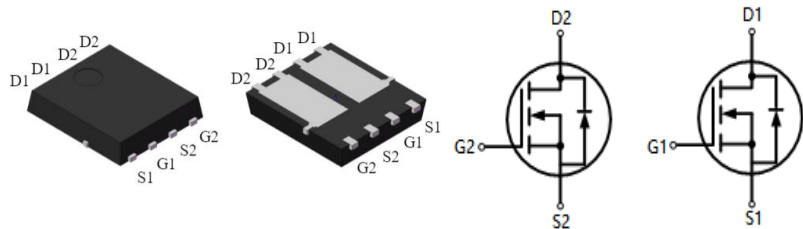
Applications

- General Automotive Applications
- Synchronous Rectifiers
- H-bridge Motor Drive

Product Summary

V_{DS}	40V
$R_{DS(on)}@10V$ typ	6.3mΩ
$R_{DS(on)}@4.5V$ typ	9.2mΩ
I_D	40A

DFN5x6双基岛



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PW068N04ESLDQ	068N04ESLDQ	DFN5*6双基岛	Tape&Reel	13 inches	12mm	5000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	40	V
Continuous drain current	I_D	72	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		40	
$T_C = 25^\circ\text{C}$ (Package limit)		40	
$T_C = 100^\circ\text{C}$ (Silicon limit)		15	
$T_a = 25^\circ\text{C}$ (See RthJA)			
Pulsed drain current ($T_C = 25^\circ\text{C}$)	$I_{D \text{ pulse}}$	160	A
Avalanche energy, single pulse ($L=0.3\text{mH}$)	E_{AS}	50	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation	P_{tot}	64	W
$T_C = 25^\circ\text{C}$		2.8	
$T_a = 25^\circ\text{C}$ (See RthJA)			
Operating junction and storage temperature	T_J, T_{stg}	-55...+175	$^\circ\text{C}$
Reflow soldering temperature (10s)	T_{sld}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	-	2.3	°C/W	-
Thermal resistance, junction - ambient	RthJA	-	53	-	°C/W	20mm x 20mm x 1.6mm 1oz single copper FR-4 PCB.

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	40	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	1.2	-	2.2	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =40V, V _{GS} =0V T _j =25°C
		-	-	100		T _j =150°C
Gate-source leakage current	I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	6.3	6.8	mΩ	V _{GS} =10V, I _D =20A
		-	9.2	12		V _{GS} =4.5V, I _D =20A
Transconductance	g _{fs}	-	48	-	S	V _{DS} =5V, I _D =20A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	880	1188	pF	V _{GS} =0V, V _{DS} =20V, f=1MHz ¹⁾
Output Capacitance	C _{oss}	-	342	462		
Reverse Transfer Capacitance	C _{rss}	-	13	30		
Gate Total Charge	Q _G	-	14	28	nC	V _{DS} =20V, I _D =20A , V _{GS} =10V
Gate-Source charge	Q _{gs}	-	3	7		
Gate-Drain charge	Q _{gd}	-	3	6		
Turn-on delay time	t _{d(on)}	-	9	-	ns	V _{GS} =10V, V _{DD} =20V, R _{G_ext} =1.6Ω, I _D =20A
Rise time	t _r	-	18	-		
Turn-off delay time	t _{d(off)}	-	24	-		
Fall time	t _f	-	6	-		
Gate resistance	R _G	-	5.5	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz

¹⁾ FT Test condition of frequency is 100KHz or 1MHz.

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	-	1.2	V	$V_{GS}=0V, I_{SD}=20A$
Body Diode Continuous Forward Current	I_S	-	-	40	A	TC = 25°C
Body Diode Pulsed Current	I_S pulse	-	-	160	A	TC = 25°C
Body Diode Reverse Recovery Time	t_{rr}	-	13	-	ns	$V_r=20V, I_f=20A,$ $dI/dt=166A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	6	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

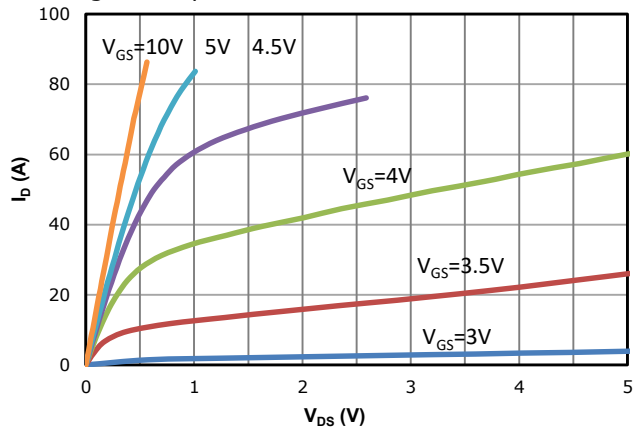


Fig 2: Transfer Characteristics

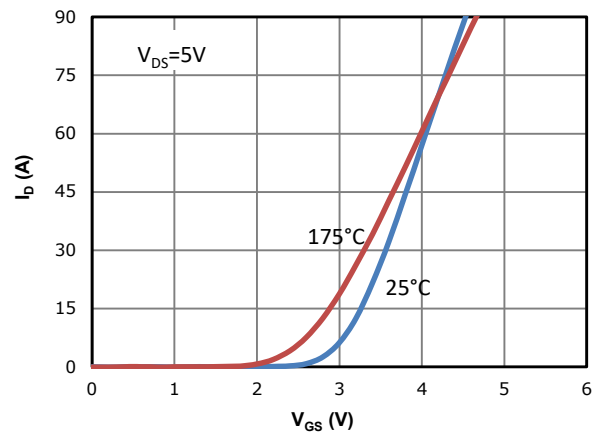


Fig 3: Rds(on) vs Drain Current and Gate Voltage

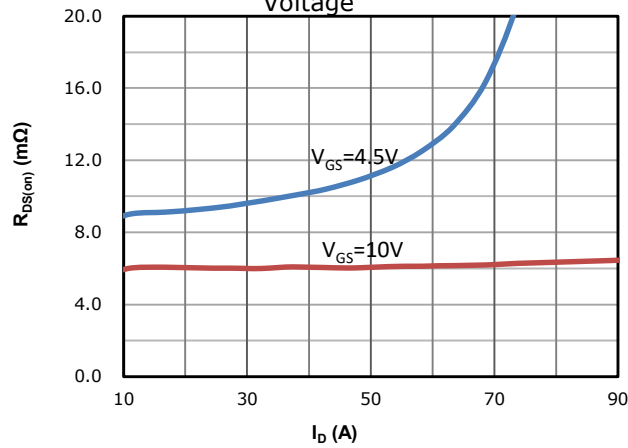


Fig 4: Rds(on) vs Gate Voltage

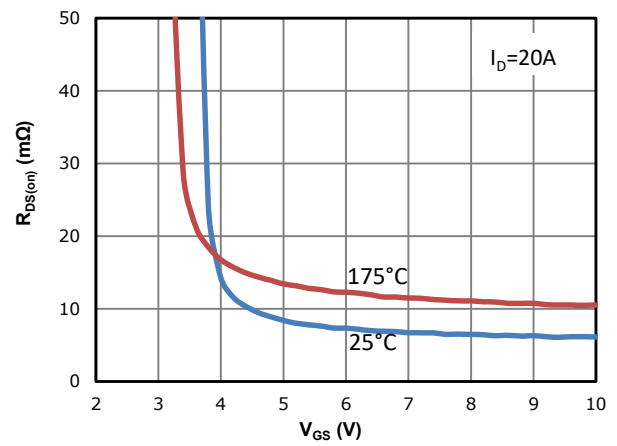


Fig 5: Rds(on) vs. Temperature

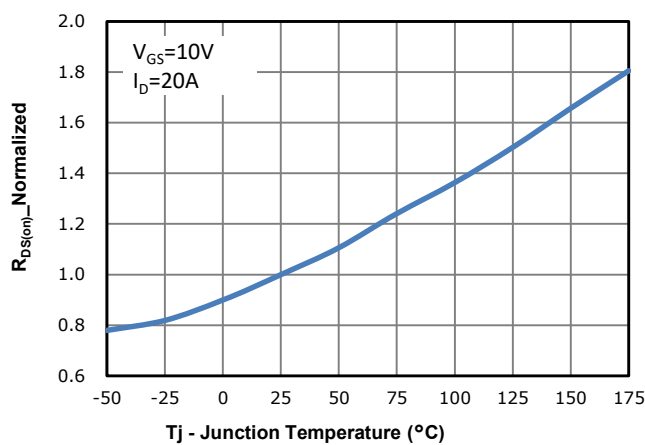


Fig 6: Vgs(th) vs. Temperature

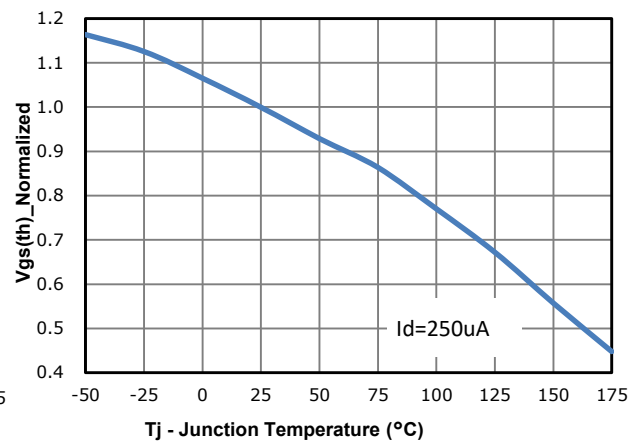


Fig 7: BVdss vs. Temperature

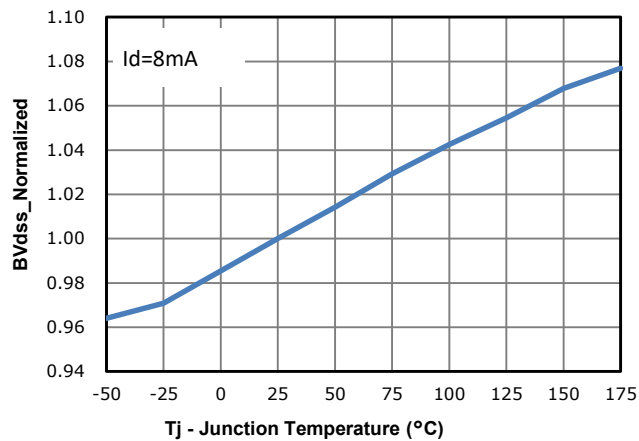


Fig 8: Capacitance Characteristics

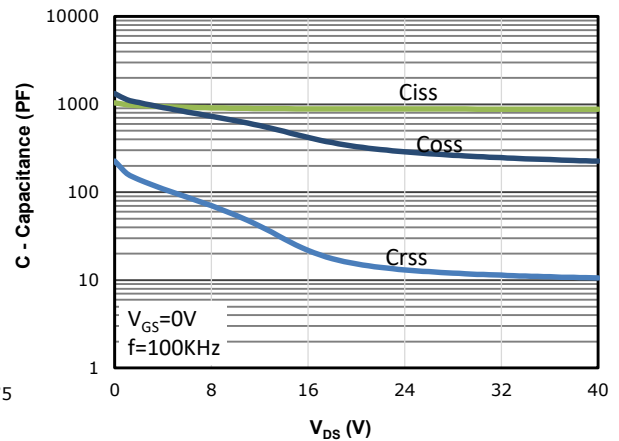


Fig 9: Gate Charge Characteristics

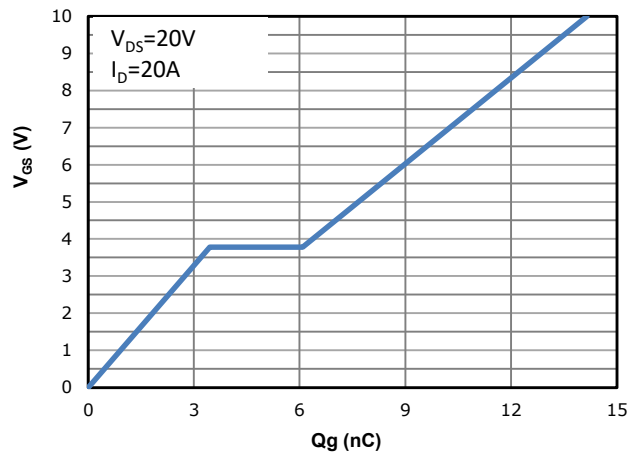


Fig 10: Body-diode Forward Characteristics

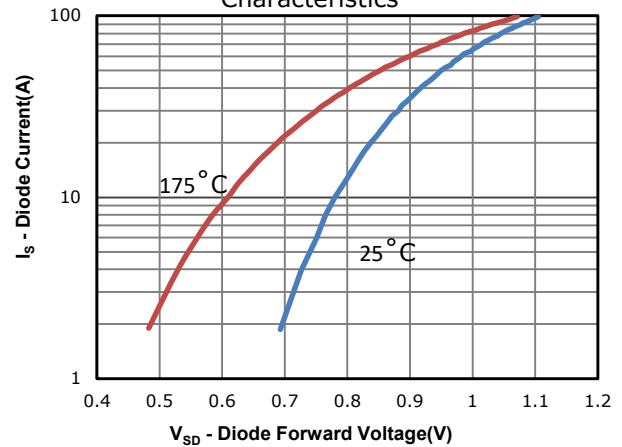


Fig 11: Power Dissipation

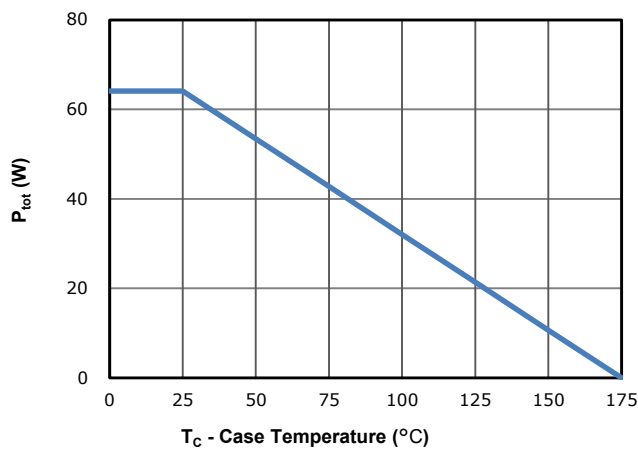


Fig 12: Drain Current Derating

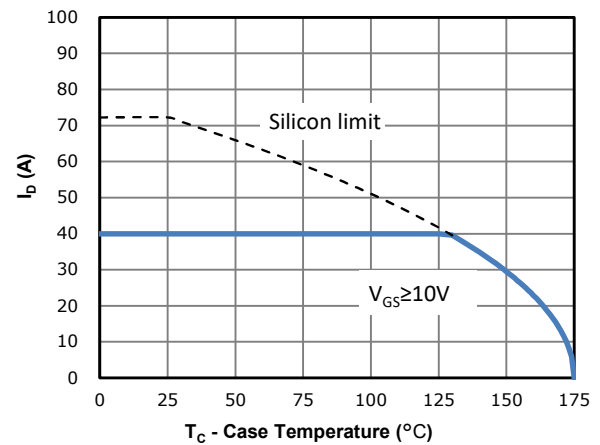


Fig 13: Safe Operating Area

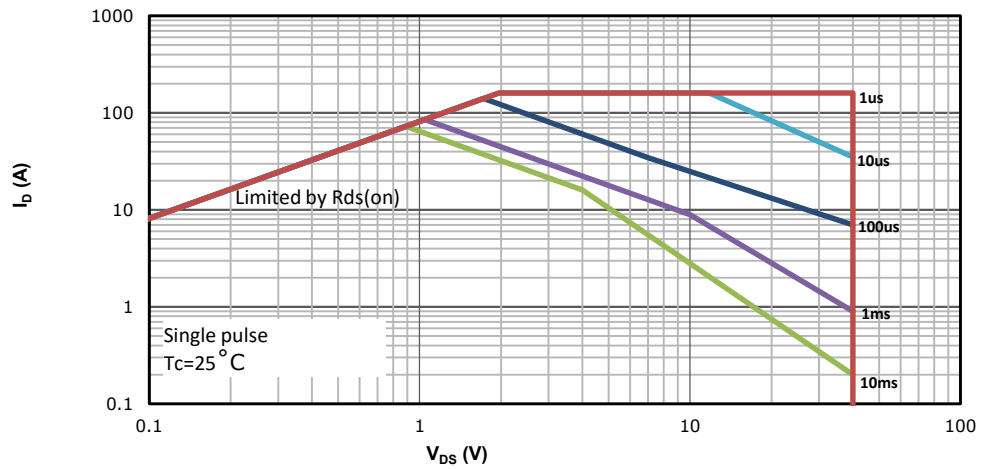
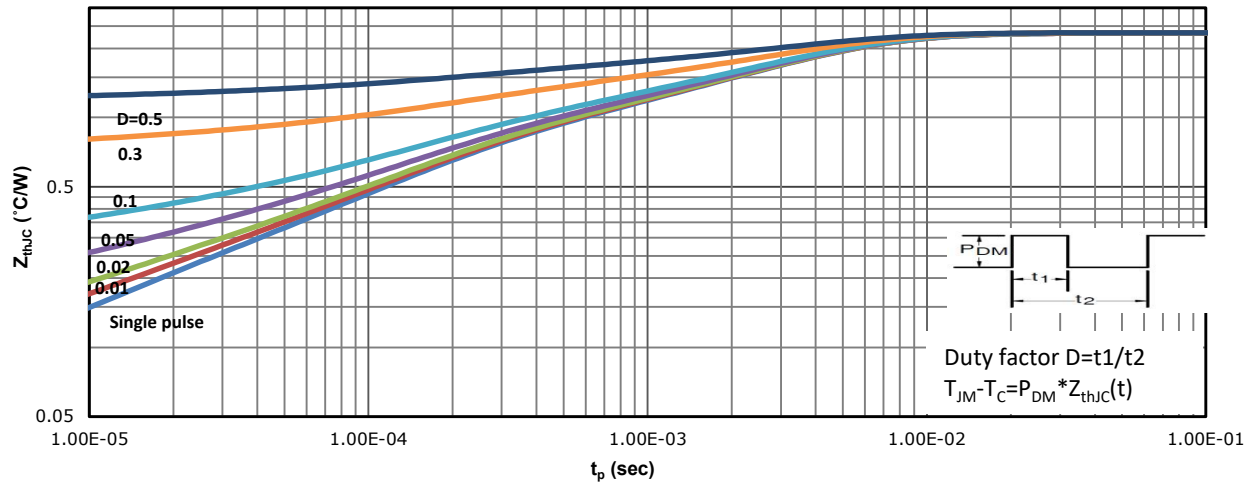
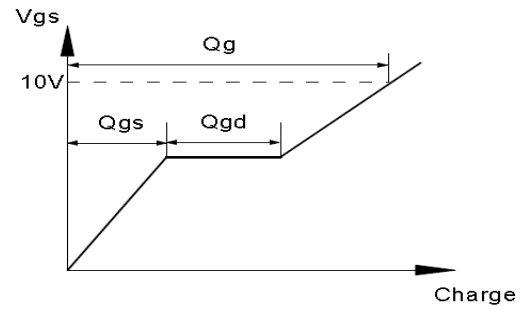


Fig 14: Max. Transient Thermal Impedance

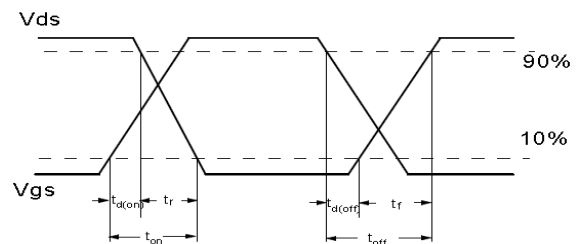


Test Circuit & Waveform

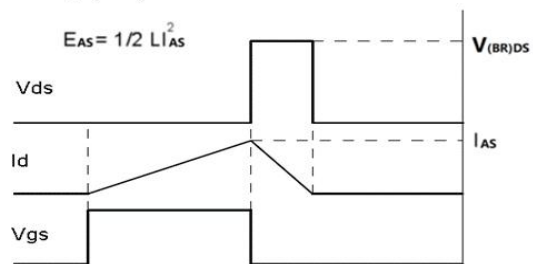
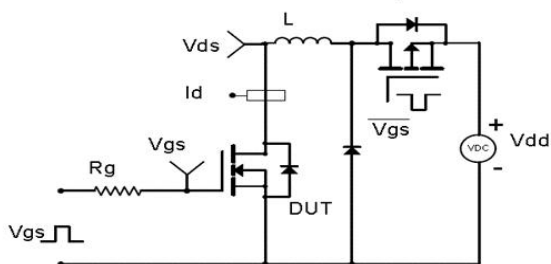
Gate Charge Test Circuit & Waveform



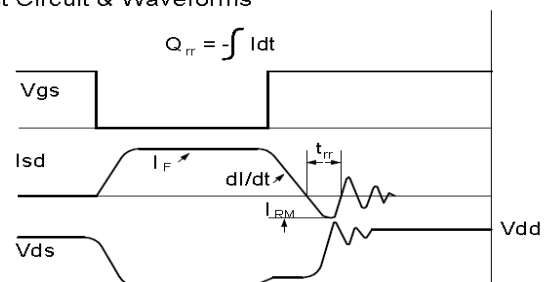
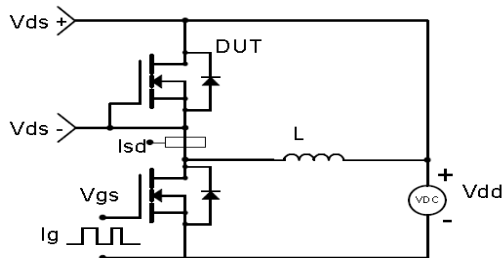
Resistive Switching Test Circuit & Waveforms

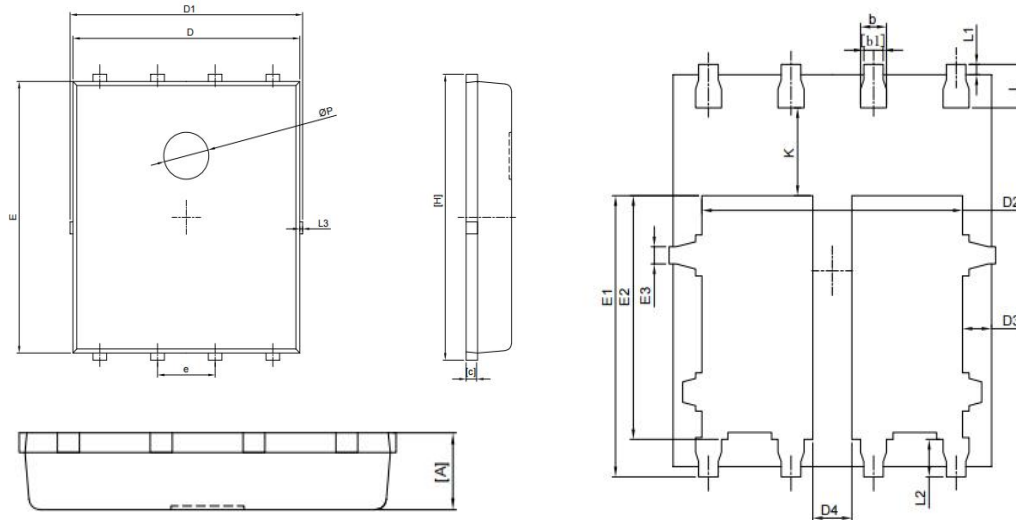


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: DFN5×6 Double Base Island Package Outline

SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.30	0.50	0.012	0.020
b1	0.20	0.40	0.008	0.016
c	0.20	0.30	0.008	0.012
D	4.80	5.20	0.189	0.205
D1	5.00	5.30	0.197	0.209
D2	3.81	4.21	0.150	0.166
D3	0.24	0.64	0.009	0.025
D4	0.45	0.75	0.018	0.030
E	5.55	5.95	0.219	0.234
E1	3.88	4.38	0.153	0.172
E2	3.32	3.82	0.131	0.150
E3	0.15	0.45	0.006	0.018
e	1.27		0.050	
H	5.95	6.15	0.234	0.242
L	0.44	0.84	0.017	0.033
L1	0.05	0.25	0.002	0.010
L2	0.35	0.75	0.014	0.030
L3	-	0.22	-	0.009
K	1.09	1.49	0.043	0.059
P	0.80	1.20	0.031	0.047

Revision History

Revision	Date	Major changes
1.4	2026/5/8	Correct dimensions of b,b1,c,D ect.
2.0	2026/6/8	Company name changed.

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

The product is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation/aerospace and life-support devices or systems.

Buyer is responsible for its products and applications using PingWei products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by PingWei.

"Typical" parameters which may be provided in PingWei data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE